CO Adsorption on MgO Thin-Films: Formation and Interaction of Surface Charged Defects

Support Information

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Figure-SI 1: Convergence tests calculated for cut-off energies of (A) the electronic densities and (B) the wave functions, (C) *k*-point mesh in First Brillouin-Zone (FBZ), and (D) bulk modulus with Murnaghan equation of state for the nonmagnetic conductor Ag bulk.

Figure-SI 2: Structural diagrams calculated for the (A) Ag, (B) MgO, (C) MgO₂, (D) Al, (E) MgAl₂O₄ and (F) Mg bulks, and the (G) unsupported MgO(001) and (H) supported MgO(001) 1×1 surfaces with 3 monolayers (ML) of MgO and 4 ML of Ag. The fixed, relaxed and vacuum regions in the surface models are showed. All structures are in a lateral vision. The structural parameters are in Table-SI 1.

	Bulks						Surfaces (001)	
	Ag	MgO	MgO ₂	Al	MgAl ₂ O ₄	Mg	3MgO	3MgO/4Ag
Space Group	Fm3m	Fm3m	Pa ₃	Fm3m	$Fd\overline{3}m$	R ₃ m	Fm3m	Fm3m
Structural								
Parameters								
a(A)	4.17	4.24	4.88	4.03	8.16	3.19	4.24	4.17
b(A)	4.17	4.24	4.88	4.03	8.16	3.19	4.24	4.17
c(A)	4.17	4.24	4.88	4.03	8.16	22.76	19.24	24.17
α (°)	90.00	90.00	90.00	90.00	90.00	90.00	90.00	90.00
β (°)	90.00	90.00	90.00	90.00	90.00	90.00	90.00	90.00
γ (°)	90.00	90.00	90.00	90.00	90.00	120.00	90.00	90.00

Table-SI 1: Structural parameters of the Ag, MgO, MgO₂, Al, and Mg bulks, and the 1×1 cells for the unsupported and supported MgO(001) surfaces calculated with PBE functional and spin-polarized.

Figure-SI 3: Top view diagrams on the optimized supercells (3×3) and (4×4) calculated for the (A) perfect, and vacancies of: (B) Mg (V_{Mg}) , (C) O (V_{O}) , and (D) $Mg + Al$ -doping $(V_{Mg} + 2Al_{Mg})^0$ at both unsupported and supported MgO(001) surfaces with 3 monolayers (ML) of MgO and 4ML of Ag. The surface Mg^{2+} and O^{2-} ions move in different directions with respect to the center of the vacancy. For the paramagnetic Mg neutral vacancy (V_{Mg}^{0}) , additional electrons were included with the charged states of paramagnetic 1- (V_{Mg}^{1-}) and diamagnetic 2- (V^{2-}_{Mg}). In the case of the diamagnetic O neutral vacancy (V^{0}_{C} \bigcirc^0 electrons missing (or holes) were considered with the states of paramagnetic $1+(V_{\Omega}^{1+})$ $\chi_{\text{O}}^{(1+)}$ and diamagnetic 2+ ($V_{\text{O}}^{(2+)}$ $V_{\rm O}^{2+}$). We considered also that the $F_{\rm O}^{0}$ \rm{C}^0 center is characterized for having a paramagnetic state (singlet), whereas the diamagnetic one (triplet) is energetically less stable at the 3MgO(001) and isoenergetic at the 3MgO(001)/4Ag(001) surfaces. Even as the Mg vacancy, we calculate for the Al-doping the Mg neutral vacancy $(V_{\text{Mg}} + 2Al_{\text{Mg}})^0$, and the charged states of 1- $(V_{\rm Mg}^{1-} + 2 \text{Al}_{\rm Mg})$ and 2- $(V_{\rm Mg}^{2-} + 2 \text{Al}_{\rm Mg})$.

Figure-SI 4: Total electrostatic potential energy averages (Hartree) in the *xy* plane (planar) computed for the 3MgO(001) and 3MgO(001)/4Ag(001) surfaces with the neutral and charged vacancies of: (A) Mg (V_{Mg}), (B) O (V_{O}), and (C) Mg + Aldoping (V_{Mg} +2Al_{Mg})⁰. The one-dimensional (macroscopic) averages, taken over one interplanar distance, are also shown for the 3MgO(001)/4Ag(001) surfaces, where the effect of the presence of an uniform compensating background charge over the macroscopic electric dipole in the slab was reduced by introducing an artificial electric double layer in the vacuum region. For correcting the potential alignment, the value of the difference between the planar average in the middle of the charged 3MgO(001) and 3MgO(001)/4Ag(001) surfaces with respect to the neutral one can be used. All slabs were moved to the box center for better visualization. 6

The transition energy $\epsilon(q/q', w)_{S,L_z}$ between charge states *q* and *q'* of a certain defect is defined by Wang, D. et al. *Phys. Rev. Lett.* **2015**, *114*, 196801, as follows:

$$
\epsilon(q/q')_{S,L_z} + \epsilon_{VBM} = \frac{\Delta E_{\text{tot}}(q, S, L_z) - \Delta E_{\text{tot}}(q', S, L_z)}{q' - q}
$$
(1)

where $\Delta E_{\text{tot}}(q, S, L_z) = \Delta E_{\text{tot}}^0 + \frac{\alpha' q^2}{\sqrt{S}}$ $\frac{q^2}{5} + \frac{\beta' q^2}{S}$ $\frac{q^2}{s}(L_z - L_z^0)$. Therefore, Equation (1) can be rewrite as follows:

$$
\epsilon(q/q')_{S,L_z} + \epsilon_{VBM} = \frac{\Delta E_{\text{tot}}^0(q) - \Delta E_{\text{tot}}^0(q')}{q' - q} + \frac{\left[\frac{\alpha'}{\sqrt{S}} + \frac{\beta'}{S}(L_z - L_z^0)\right](q^2 - q'^2)}{q' - q}
$$
(2)

Since energy corrections due to supercell Coulomb interactions should scale as *q* 2 , we propose that *α* and *β* should have the following dependence on *q* and *q* ′ :

$$
\alpha = \frac{\alpha'(q^2 - q'^2)}{q' - q} \n\beta = \frac{\beta'(q^2 - q'^2)}{q' - q}
$$
\n(3)

where the values of α' , β' , and L_z^0 do not change regardless charge state, for a same type of defect. We assume that *α*' and *β*' do not depend on the specific type of defect, but only on the slab composition (MgO or MgO/Ag), which indeed would affect screening. Hence, $\epsilon(q/q')_0$ does not depend on S and L_Z in any transition.

$$
\epsilon(q/q')_0 + \epsilon_{VBM} = \frac{\Delta E_{\text{tot}}^0(q) - \Delta E_{\text{tot}}^0(q')}{q' - q}
$$
(4)

This allows us to reduce the number of DFT calculations needed to determine *α* and *β* for all defects. Therefore, *α'*, *β'*, and L_Z^0 were calculated only for the L_Z and *S* variations in the MgO and MgO/Ag slabs from the (0, 1−) transition in *V*_{Mg} (Figure-SI 5). So, we use the *α*, *β*, and L_2^0 $\frac{0}{Z}$ values to obtain $\epsilon(q/q')_0$ for all charge state transitions in all defects at the MgO and MgO/Ag surfaces.

$$
\epsilon(q/q')_{S,L_z} = \epsilon(q/q')_0 + \frac{\alpha}{\sqrt{S}} + \frac{\beta}{S}(L_z - L_z^0)
$$

$$
= \epsilon(q/q')_0 + \frac{\alpha}{\sqrt{S}} + \frac{\beta L_z}{S} - \frac{C}{S}
$$
(5)

where $C = \beta L_z^0$ and $\epsilon (q/q')_0$ is the "true" transition energy.

For the MgO and MgO/Ag slabs, the values calculated for $\epsilon (q/q')_0$ are shown in Table-SI 2. These values were then used to move the curves of formation energy (ΔE_{for}^q (defect) in Equation (1) in main text) so that the transitions of the charge states match the calculated $\epsilon (q/q')_0$.

Figure-SI 5: Curves of transition energy ($\epsilon(q/q')_{S,L_z}$) for the transition of charge ϵ (0/1−) through different supercell sizes: (3 × 3), (4 × 4), (5 × 5) and (6 × 6) for the MgO slab (triangle); and (3×3) , (4×4) and (5×5) for the 3MgO/4Ag slab (circle). The vacuum layer size was also increased. The terms of total energy of the slabs of vacancy with charge q and q' ($\Delta E_{tot}(q$, vacancy) and ∆E_{tot}(q', vacancy)) were obtained without further optimization of the surfaces.

		$\epsilon (q/q')_0$ (eV)		
Defect	Charge Transition	MgO	MgO/Ag	
$V_{\rm Mg}$	$(0,1-)$	1.36	0.35	
	$(1-, 2-)$	6.69	4.73	
V_{Ω}	$(2+, 1+)$	-6.68	-7.89	
	$(1+,0)$	-1.67	0.38	
$(V_{\rm Mg}+2{\rm Al}_{\rm Mg})^0$	$(0,1-)$	3.76	0.58	
	$(1-, 2-)$	7.67	2.42	

Table-SI 2: Values of $\epsilon(q/q^{'})_0$ in eV calculated for each transition of charge state in the vacancies of Mg (V_{Mg}), O (V_{O}), and Mg + Al-doping (V_{Mg} +2Al_{Mg})⁰.

Figure-SI 6: (A) Total electrostatic potential energy averages (Hartree) in the *xy* plane (planar) computed for the the Ag bulk and the 4Ag(001) surface. The one-dimension (macroscopic) averages are also showed, where it was reduced by introducing an artificial electric double layer in the vacuum region. The slab was moved to the box center for better visualization. (B) Phase diagram calculated for the formation of the elemental bulk phases of the magnesium oxide (MgO) and magnesium peroxide (MgO₂) under the range of the $\Delta \mu_{Mg}$ and $\Delta \mu_{\rm O_2}$ chemical potentials between the O-rich (Δ $\mu_{\rm O_2}$ =0) and Mg-rich (Δ $\mu_{\rm Mg}$ =0) conditions as indicated by labels A and B, respectively.

Figure-SI 7: Projected density of states (PDOS) calculated for the slabs of the perfect 3MgO(001) and 3MgO(001)/4Ag(001) surfaces. For the thin-film, we also accounted the MgO/Ag interface. Mg (5C) and O (5C) represent the fivecoordinated Mg and \breve{O} sites at the surface, respectively; while Mg (6C), O (6C) and Ag (6C) represent the six-coordinated Mg, O, and Ag sites at the interface, respectively.